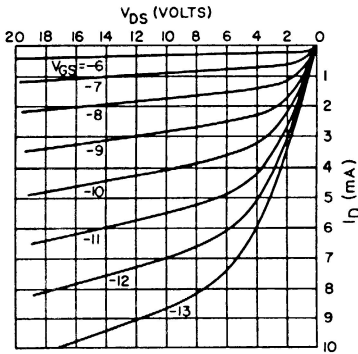
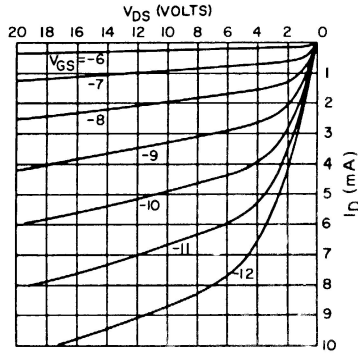


## TYPICAL CHARACTERISTIC CURVES

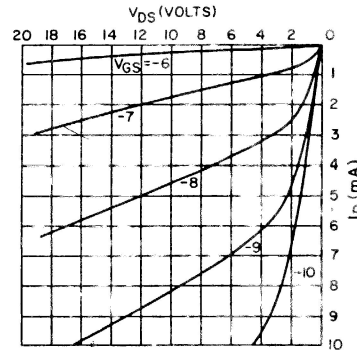
DRAIN CHARACTERISTICS AT +125 °C



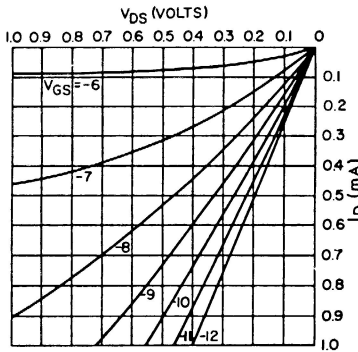
DRAIN CHARACTERISTICS AT 25 °C



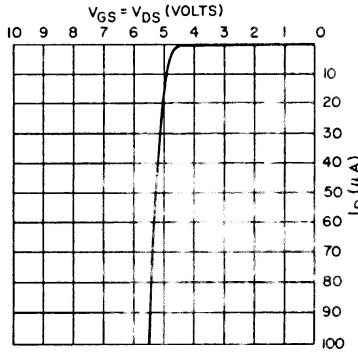
DRAIN CHARACTERISTICS AT -200 °C



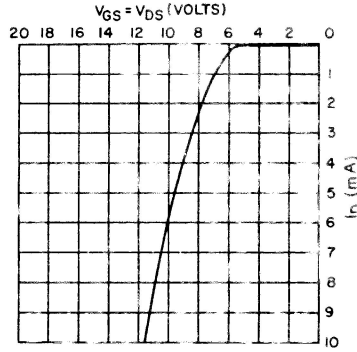
DRAIN CHARACTERISTICS AT 25 °C



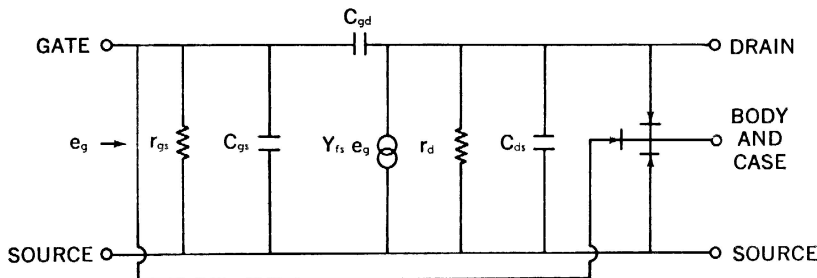
TURN-ON CHARACTERISTICS AT 25 °C



TURN-ON CHARACTERISTICS AT 25 °C



### SMALL SIGNAL EQUIVALENT CIRCUIT (Conditions: $V_{GS} = V_{DS} = 10V$ )



SYMBOL		TYPICAL VALUE	UNITS
Diodes	All diodes are to be considered perfect diodes		
$r_{gs}$	Gate to source leakage resistance and diode leakage resistance	$10^{10}$	ohms
$r_d$	Dynamic drain resistance	25	Kohms
$C_{gs}$	Gate to source capacitance	2.25	pf
$C_{gd}$	Gate to drain capacitance	1.5	pf
$C_{ds}$	Drain to source capacitance	1.25	pf
$Y_{fs}$	Forward transadmittance	2500	$\mu$ mho

### HANDLING PRECAUTIONS

The MEM 511 insulated gate field effect transistors have been designed with an integrated zener diode clamp from the high input resistance ( $10^{15}$  ohm typical) gate, to the body which is internally connected to the case. This clamp eliminates the detrimental effects of high electrostatic voltages on the gate that can be generated in normal handling.

It is recommended that the body (lead 3) be connected to the source (lead 4) for most applications.

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